

## TPS65135 单电感器、多路输出稳压器

### 1 特性

- 单电感器、多路输出拓扑
- 输入电压范围：2.5V 至 5.5V
- $V_I = 2.9V$  时，输出功率为 750mW
- 输出的正电压高达 6V
- 输出的负电压低至 -7V
- 输出电压精度为 1%
- 允许的输出电流失配高达 50%
- 出色线路稳压
- 用于实现轻负载效率的高级节电模式
- 低噪声运行
- 无声模式
- 短路保护功能
- 热关断
- 3mm x 3mm 超薄 QFN 封装

### 2 应用

- AMOLED 显示电源
- LCD 电源
- 分离轨电源，适用于运算放大器、数据转换器、数据接口等。

### 3 说明

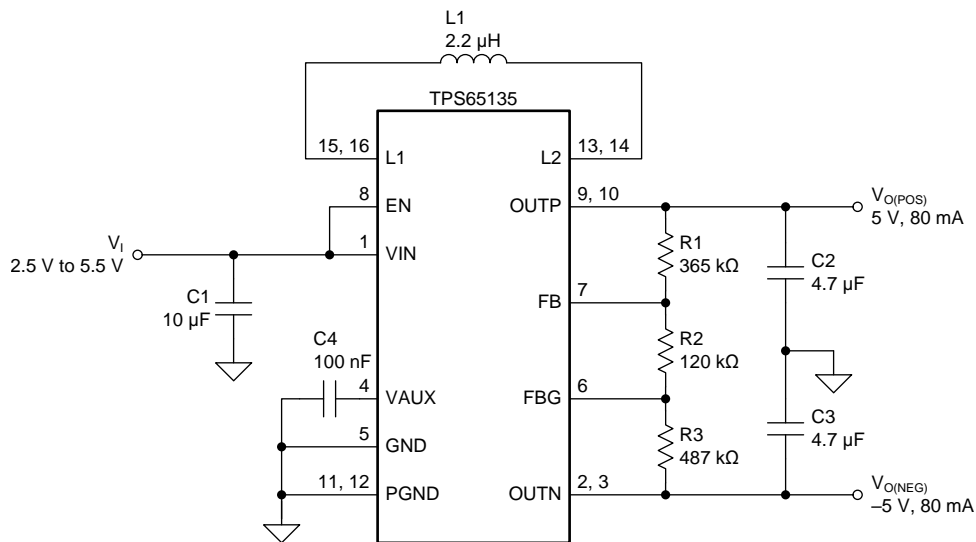
TPS65135 器件是一款高效的分离轨电源。该转换器具有单电感器和多输出 (SIMO) 拓扑，因此使用的外部组件极少。该器件采用降压/升压拓扑，并生成高于或低于输入电源电压的正负输出电压。SIMO 拓扑可实现出色的线路和负载调节，这一特性非常必要，例如，可避免移动通信系统在传输阶段产生的输入电压偏差对手机显示的干扰。如果两轨之间的输出电流失配小于 50%，该器件也可用作通用分离轨电源。

#### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
TPS65135	WQFN (16)	3.00mm x 3.00mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

#### 典型应用电路原理图



Copyright © 2017, Texas Instruments Incorporated



## 目录

<b>1</b>	特性 .....	<b>1</b>	7.4	Device Functional Modes.....	<b>11</b>
<b>2</b>	应用 .....	<b>1</b>	<b>8</b>	<b>Application and Implementation</b> .....	<b>12</b>
<b>3</b>	说明 .....	<b>1</b>	8.1	Application Information.....	<b>12</b>
<b>4</b>	修订历史记录 .....	<b>2</b>	8.2	Typical Application .....	<b>12</b>
<b>5</b>	<b>Pin Configuration and Functions</b> .....	<b>3</b>	<b>9</b>	<b>Power Supply Recommendations</b> .....	<b>19</b>
<b>6</b>	<b>Specifications</b> .....	<b>4</b>	<b>10</b>	<b>Layout</b> .....	<b>19</b>
6.1	Absolute Maximum Ratings .....	<b>4</b>	10.1	Layout Guidelines .....	<b>19</b>
6.2	ESD Ratings.....	<b>4</b>	10.2	Layout Example .....	<b>20</b>
6.3	Recommended Operating Conditions.....	<b>4</b>	<b>11</b>	器件和文档支持 .....	<b>21</b>
6.4	Thermal Information .....	<b>4</b>	11.1	器件支持 .....	<b>21</b>
6.5	Electrical Characteristics.....	<b>5</b>	11.2	接收文档更新通知 .....	<b>21</b>
6.6	Typical Characteristics .....	<b>6</b>	11.3	社区资源.....	<b>21</b>
<b>7</b>	<b>Detailed Description</b> .....	<b>7</b>	11.4	商标.....	<b>21</b>
7.1	Overview .....	<b>7</b>	11.5	静电放电警告.....	<b>21</b>
7.2	Functional Block Diagram .....	<b>8</b>	11.6	Glossary .....	<b>21</b>
7.3	Feature Description.....	<b>9</b>	<b>12</b>	机械、封装和可订购信息.....	<b>21</b>

## 4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

### Changes from Revision B (June 2015) to Revision C

Page

- Changed L2 pin numbers From: 1 and 14 To: 13 and 14 in the *Pin Functions* table ..... **3**
- Changed PGND pin numbers From: 11 and 11 To: 11 and 12 in the *Pin Functions* table..... **3**

### Changes from Revision A (November 2011) to Revision B

Page

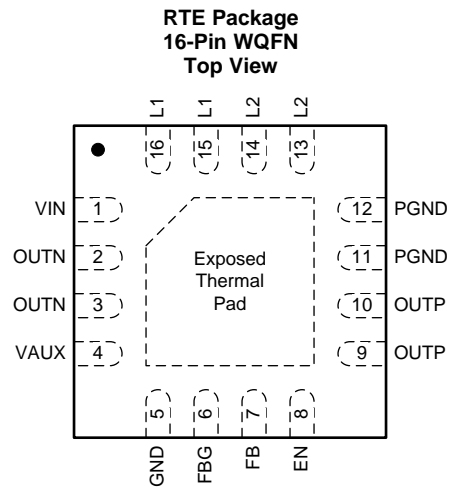
- 已添加 引脚配置和功能部分、ESD 额定值表、特性描述部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分 ..... **1**
- Moved output current mismatch to Recommended Operating Conditions .....

### Changes from Original (November 2011) to Revision A

Page

- Changed the UVLO threshold max value for  $V_{IN}$  falling From: 2 V To 2.1 V ..... **5**

## 5 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN	8	I	Input pin to enable the device. Pulling this pin high enables the device. This pin has an internal 500-k $\Omega$ pull-down resistor.
FB	7	I	Feedback regulation point for the positive output voltage rail
FBG	6	I	Feedback regulation point for the negative output voltage rail
GND	5	–	Analog ground
L1	15	I/O	Inductor terminal
	16		
L2	13	I/O	Inductor terminal
	14		
OUTN	2	O	Negative output
	3		
OUTP	9	O	Positive output
	10		
PGND	11	–	Power ground
	12		
VAUX	4	I/O	Reference voltage output. This pin requires a 100-nF capacitor for stability.
VIN	1	I	Input supply
Exposed thermal pad	—	–	Connect this pad to ground

## 6 Specifications

### 6.1 Absolute Maximum Ratings<sup>(1)(2)</sup>

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Voltage	VIN, EN, VAUX, FB, OUTP, L2	-0.3	7	V
	L1, OUTN	-8	7	V
	FBG	-0.3	0.3	V
Operating junction temperature, T <sub>J</sub>		-40	150	°C
Operating ambient temperature, T <sub>A</sub>		-40	85	°C
Storage temperature, T <sub>stg</sub>		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to ground.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	
	Machine model (MM)	±200	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

		MIN	TYP	MAX	UNIT
V <sub>I</sub>	Input voltage range	2.5		5.5	V
I <sub>O(POS)</sub> / I <sub>O(NEG)</sub>	Output current mismatch	0.5		2	
P <sub>O</sub>	Output power (V <sub>I</sub> = 2.9 V, V <sub>O(POS)</sub> – V <sub>O(NEG)</sub> ≤ 10 V)			750	mW
L	Inductor <sup>(1)</sup>	1	2.2	4.7	μH
C <sub>(IN)</sub>	Input Capacitor <sup>(1)</sup>	4.7	10		μF
C <sub>O(POS)</sub> , C <sub>O(NEG)</sub>	Output Capacitors <sup>(1)</sup>	4.7	10	20	μF
T <sub>A</sub>	Operating ambient temperature	-40		85	°C
T <sub>J</sub>	Operating junction temperature	-40		125	°C

- (1) Please refer to [Application Information](#) for further information

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS65135	UNIT
		RTE (WQFN)	
		16 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	44.8	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	42	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	4.3	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	16.9	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	0.4	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	16.8	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

$V_I = 3.7\text{ V}$ ,  $V_{(EN)} = V_I$ ,  $V_{O(POS)} = 5\text{ V}$ ,  $V_{O(NEG)} = -5\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ; typical values are at  $T_A = 25^\circ\text{C}$  (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENT</b>						
$V_I$	Input voltage range		2.5		5.5	V
$I_{I(\text{standby})}$	Quiescent current	EN = H; measured into VIN pin		7		mA
	Shutdown current	EN = L; measured into VIN pin		0.1	2	$\mu\text{A}$
<b>UNDERVOLTAGE LOCKOUT</b>						
	Input threshold voltage (VIN) (undervoltage lockout)	$V_I$ rising		2	2.3	V
		$V_I$ falling		1.8	2.1	V
<b>THERMAL SHUTDOWN</b>						
	Thermal shutdown junction temperature			140		$^\circ\text{C}$
	Thermal shutdown hysteresis			5		$^\circ\text{C}$
<b>ENABLE</b>						
	High-level input voltage (EN)	$V_I = 2.5\text{ V}$ to $5.5\text{ V}$	1.2			V
	Low-level input voltage (EN)	$V_I = 2.5\text{ V}$ to $5.5\text{ V}$			0.4	V
$R_{(EN)}$	Pull-down resistor (EN)		200	500	900	$\text{k}\Omega$
<b>OUTPUT</b>						
$V_{O(POS)}$	Positive output voltage range		3		6	V
	Threshold voltage (OUTP) (overvoltage protection)	$I_{O(POS)} = 10\text{ mA}$	6.1	7		V
$V_{O(NEG)}$	Negative output voltage range		-7		-2.5	V
	Threshold voltage (OUTN) (overvoltage protection)	$I_{O(NEG)} = -10\text{ mA}$		-7.6	-7.1	V
$V_{\text{ref1}}$	Positive output reference voltage		-1%	1.24	+1%	V
$V_{\text{ref2}}$	Negative output reference voltage		-10	0	10	mV
	MOSFET on-state resistance (Q1)	$I_{D(Q1)} = 100\text{ mA}$		250		$\text{m}\Omega$
	MOSFET on-state resistance (Q2)	$I_{D(Q2)} = 100\text{ mA}$		200		$\text{m}\Omega$
	MOSFET on-state resistance (Q3)	$I_{D(Q3)} = 100\text{ mA}$		500		$\text{m}\Omega$
	MOSFET on-state resistance (Q4)	$I_{D(Q4)} = 100\text{ mA}$		300		$\text{m}\Omega$
$I_{D(Q2)\text{max}}$	Q2 switch current limit	$V_I = 3.7\text{ V}$	0.9	1.2	1.6	A
		$V_I = 2.5\text{ V}$	1	1.5	1.9	

## 6.6 Typical Characteristics

$V_I = 3.7\text{ V}$  and  $T_A = 25^\circ\text{C}$  unless otherwise noted

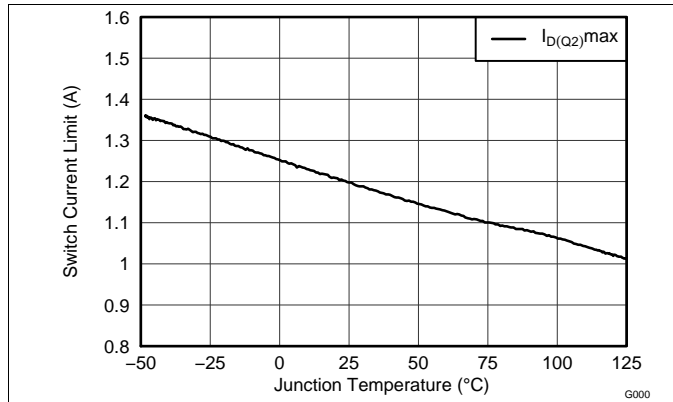


Figure 1. Switch Current Limit vs Temperature

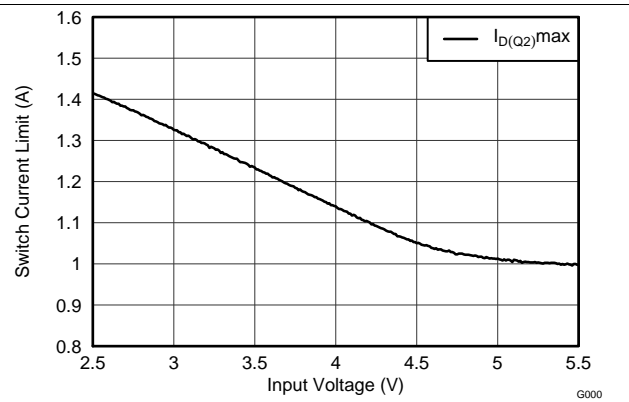


Figure 2. Switch Current Limit vs Input Supply Voltage

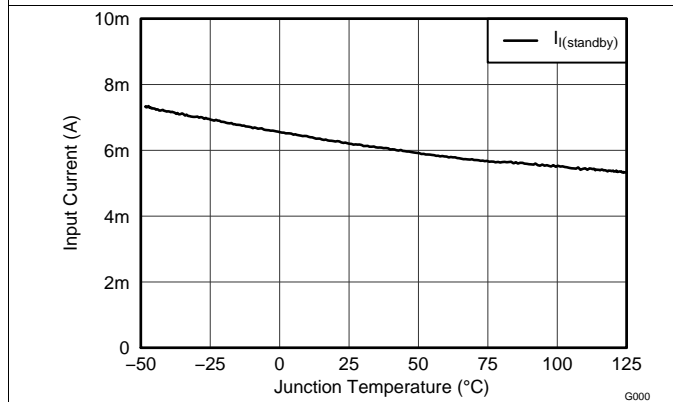


Figure 3. Input Supply Current vs Temperature

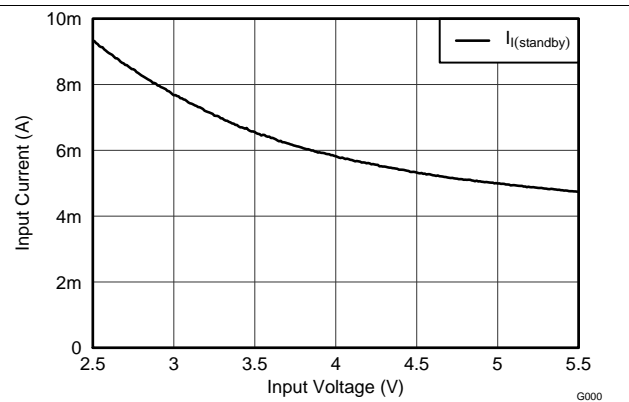


Figure 4. Input Supply Current vs Input Supply Voltage

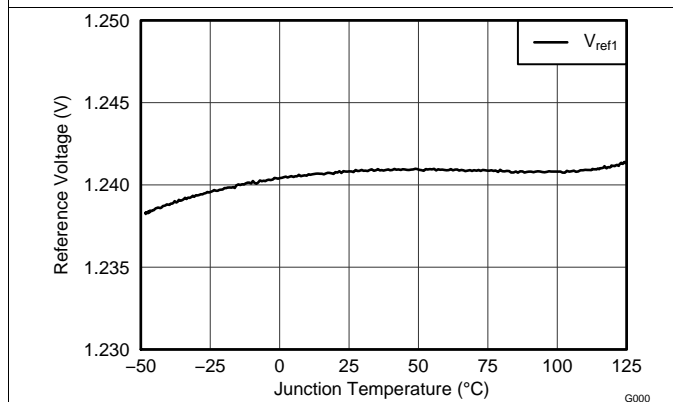


Figure 5. Reference Voltage  $V_{ref1}$  vs Temperature

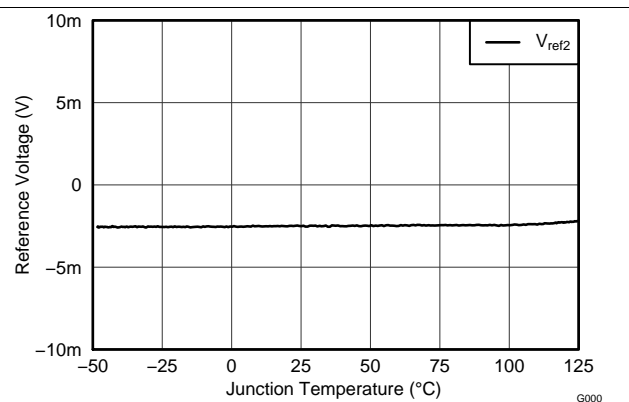


Figure 6. Reference Voltage  $V_{ref2}$  vs Temperature

## 7 Detailed Description

### 7.1 Overview

The TPS65135 device uses a four-switch buck-boost converter topology to generate one negative and one positive output voltage with a single inductor. The device uses a SIMO topology to achieve excellent line transient response, buck-boost mode for both outputs, and high efficiency over the entire output current range. High efficiency over the entire load-current range is implemented by reducing the converter switching frequency under low load conditions. Out-of-audio mode prevents the switching frequency going below 20 kHz.

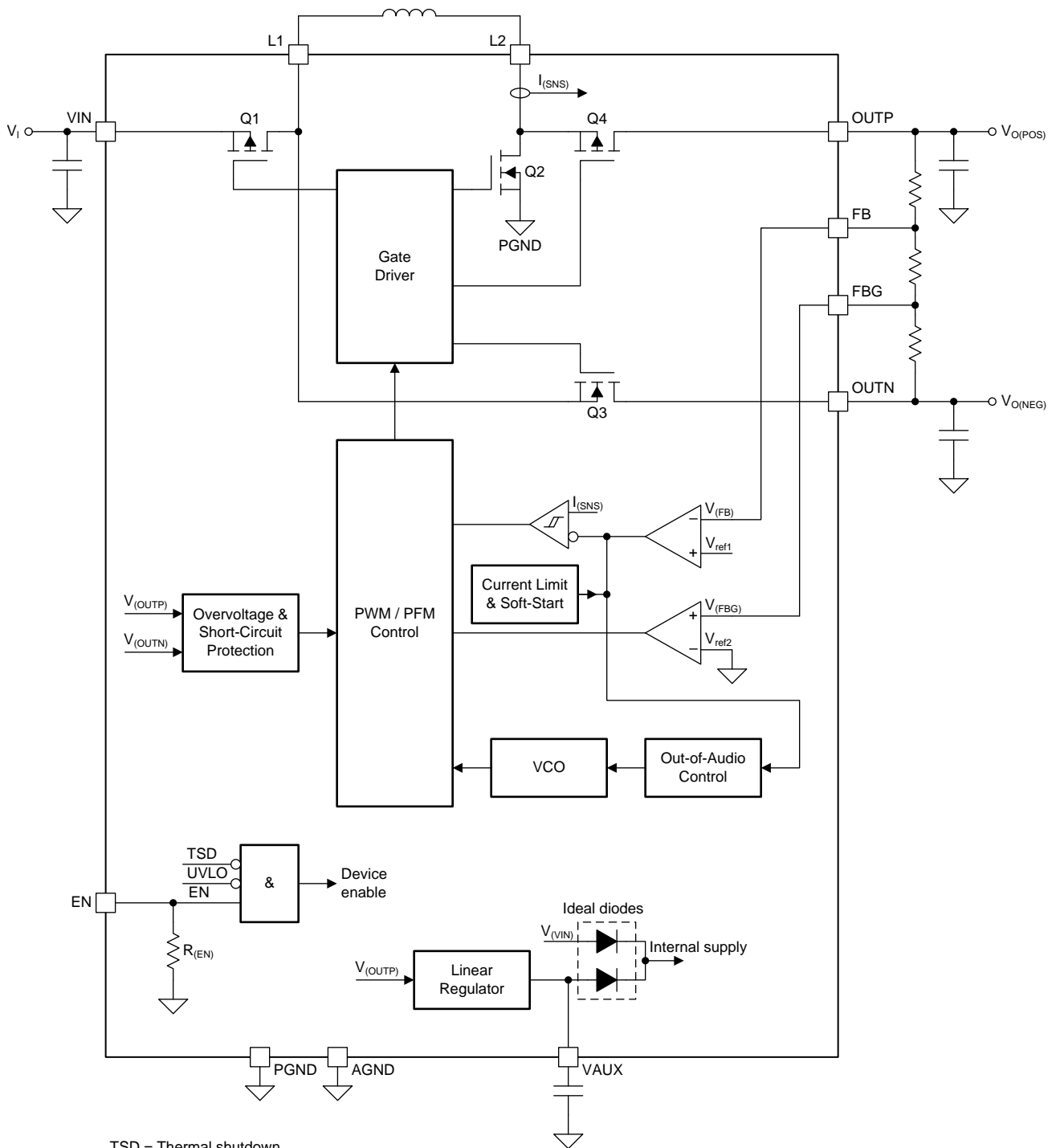
The converter operates with two control loops. One error amplifier controls the positive output voltage  $V_{O(POS)}$  so that the FB pin is regulated to 1.24 V. A second error amplifier controls the negative output voltage  $V_{O(NEG)}$  so that the FBG pin is regulated to 0 V. An external feedback divider allows both output voltages to be set to the desired value. In principle, the SIMO converter topology operates just like any other buck-boost converter topology, with the difference that the output voltage across the inductor is the sum of the positive and negative output voltages. With this consideration all calculations of the buck-boost converter apply for this topology as well. During the first part of a switching cycle Q1 and Q2 are closed, connecting the inductor from  $V_I$  to ground. During the second part of a switching cycle, the inductor discharges to the positive and negative outputs by closing switches Q4 and Q3. Because the inductor is discharged to both of the outputs simultaneously, the output voltages can be higher or lower than the input voltage. The converter operates best when the positive output current  $I_{O(POS)}$  is equal to the negative output current  $I_{O(NEG)}$ , for example, as is the case when driving an AMOLED display. However, asymmetries of up to 50% in load current can be canceled out by the used topology. In such cases, a third part of the switching cycle is implemented, during which either Q3 is turned off and Q1 is turned on (as is the case when  $I_{O(POS)} > I_{O(NEG)}$ ) or Q4 is turned off and Q2 is turned on (as is the case when  $I_{O(NEG)} > I_{O(POS)}$ ) (see [Table 1](#)).

During light loads the converter operates in DCM, using peak-current control and a switching frequency determined by a voltage-controlled oscillator (VCO). At higher load currents the converter operates in CCM with a switching frequency controlled by a fixed off-time. The SIMO regulator topology achieves its best line transient response when operating in DCM.

**Table 1. Switch Control**

Switching Cycle	Q1	Q2	Q3	Q4	Remark
Part 1	On	On	Off	Off	
Part 2	Off	Off	On	On	
Part 3	On	Off	Off	On	If $I_{O(POS)} >  I_{O(NEG)} $
	Off	On	On	Off	If $ I_{O(NEG)}  > I_{O(POS)}$

7.2 Functional Block Diagram



TSD = Thermal shutdown.  
UVLO = Undervoltage lockout.

Copyright © 2017, Texas Instruments Incorporated



### 7.3 Feature Description

#### 7.3.1 Advanced Power-Save Mode for Light-Load Efficiency

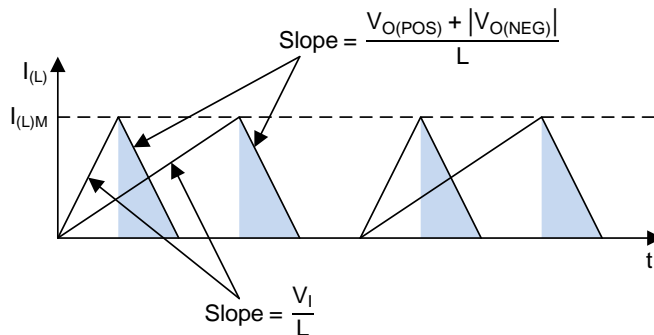
In order to maintain high efficiency over the entire load current range, the converter reduces its switching frequency as the load current decreases. The advanced power-save mode controls the switching frequency using a voltage-controlled oscillator (VCO). The VCO frequency is proportional to the inductor peak current, with a lower frequency limit of 20 kHz; but in typical applications the frequency does not go below 100 kHz. This avoids disturbance of the audio band and minimizes audible noise coming from the ceramic input and output capacitors. By maintaining a controlled switching frequency, potential EMI is minimized. This is especially important when using the device in mobile phones. See Figure 24 for typical switching frequency versus load current. For zero load an internal shunt regulator ensures stable output voltage regulation.

#### 7.3.2 Buck-Boost Mode Operation

Buck-boost mode operation allows the input voltage to be higher or lower than the output voltage. This mode allows the use of batteries and supply voltages that are above the positive output voltage.

#### 7.3.3 Inherently Good Line-Transient Regulation

The SIMO regulator achieves inherently good line-transient response when operating in discontinuous conduction mode (DCM), as shown in Figure 14 and Figure 15. In DCM, the current delivered to the output is determined by the peak value and slope of the inductor current. This is illustrated in Figure 7, where the average output current, shown by the shaded area, is the same for different input voltages. Because the converter uses peak-current-mode control, the peak current is fixed as long as the load current is fixed. The falling slope of the inductor current is given by the difference between the positive and negative output voltages and the inductor value; it is independent of the input voltage. As a result, any change in input voltage changes the converter duty cycle but not the peak value or slope of the inductor current when discharging. The average output current, given by the area A (Figure 7), therefore remains constant over any input voltage variation. Entering continuous conduction mode (CCM) linearly decreases the line-transient performance; however, the line-transient response in CCM is still as good as any standard current-mode switching converter.



**Figure 7. Inherently Good Line-Transient Regulation**

The following formulas describe the operation of the TPS65135 device when operating in CCM with equal positive and negative output currents. The converter always sees the sum  $V_O$  of the magnitude of the positive and negative output voltages, as given by

$$V_O = V_{O(POS)} + |V_{O(NEG)}|$$

where

- $V_{O(POS)}$  is the positive output voltage
- and  $V_{O(NEG)}$  is the negative output voltage.

(1)

The converter duty cycle is calculated using the efficiency estimation from datasheet curves or from real application measurements. A value of 70% for the efficiency  $\eta$  is a good starting assumption for most applications.

## Feature Description (continued)

$$D = \frac{V_O}{\eta V_I + V_O}$$

where

- D is the duty cycle of Q2
- and  $\eta$  is the converter efficiency. (2)

Now the output current for entering CCM can be calculated. The switching frequency can be obtained from the data sheet graphs. A frequency of 1.5 MHz is a good assumption for these calculations.

$$I_{O(\text{CCM})} = \frac{V_O(1-D)^2}{2fL}$$

where

- $I_{O(\text{CCM})}$  is the value of output current at which continuous conduction starts;
- f is the converter switching frequency;
- and L is the inductance connected between the L1 and L2 pins. (3)

The inductor ripple current when operating in CCM can also be calculated

$$I_{(L)(\text{PP})} = \frac{DV_I}{fL}$$

where

- $I_{(L)(\text{PP})}$  is the peak-to-peak (that is, ripple) inductor current. (4)

Finally, the converter switch peak current can be calculated

$$I_{(L)M} = \frac{I_O}{1-D} + \frac{I_{(L)(\text{PP})}}{2}$$

where

- $I_{(L)M}$  is the peak (that is, maximum) inductor current. (5)

### 7.3.4 Overvoltage Protection

The device monitors the positive and negative output voltages and reduces the current limit when either (or both) of the output voltages exceeds its overvoltage protection threshold. The positive output voltage is clamped to 7 V and the negative output voltage to -7.6 V.

### 7.3.5 Short-Circuit Protection

Both outputs are protected against short circuits either to ground or to the other output. The device's switching frequency and current limit are reduced in case of a short circuit.

### 7.3.6 Soft-Start Operation

The device increases the current limit during soft-start operation to avoid high inrush currents during start up. The current limit typically ramps up to its maximum value within 100  $\mu$ s.

## Feature Description (continued)

### 7.3.7 Output-Current Mismatch

The device operates best when the current of the positive output is similar to the current of the negative output. However, the device is able to regulate an output current mismatch of up to 50% (See [Figure 26](#) for typically allowed currents, only 50% mismatch is specified). If the output-current mismatch becomes much larger one of the outputs goes out of regulation and finally the device shuts down. In case of zero load of one output the other output can support up to 5 mA. The device automatically recovers when the mismatch is reduced. The formula below can be used to calculate the maximum supported current mismatch.

$$0.5 \leq \frac{|I_{O(POS)}|}{|I_{O(NEG)}|} \leq 2 \quad (6)$$

### 7.3.8 Setting the Output Voltages

The output voltages are set by the three feedback resistors R1, R2, and R3 ([Figure 8](#)). R1 and R2 set the positive output voltage  $V_{O(POS)}$  and R2 and R3 set the negative output voltage  $V_{O(NEG)}$ . To reduce the circuit's sensitivity to noise, it is recommended to choose R2 so that a current of at least 10  $\mu\text{A}$  flows through the feedback resistors. [Equation 7](#) can be used to calculate a suitable value for R2.

$$R2 = \frac{V_{ref1}}{I_{(R2)}} = \frac{1.24 \text{ V}}{10 \mu\text{A}} = 124 \text{ k}\Omega \quad (7)$$

The positive output voltage  $V_{O(POS)}$  is given by

$$V_{O(POS)} = V_{ref1} \left( 1 + \frac{R1}{R2} \right) \quad (8)$$

The negative output voltage  $V_{O(NEG)}$  is given by

$$V_{O(NEG)} = -V_{ref1} \left( \frac{R3}{R2} \right) \quad (9)$$

## 7.4 Device Functional Modes

### 7.4.1 Operation with $2.5 \text{ V} \leq V_I \leq 5.5 \text{ V}$

The recommended input supply voltage is 2.5 V to 5.5 V. Within this range the device operates normally and achieves its specified performance.

### 7.4.2 Operation with $V_I < 2.5 \text{ V}$

The recommended minimum input supply voltage is 2.5 V. The device continues to operate with input supply voltages lower than 2.5 V, however, its performance is not specified. The device does not operate with input supply voltages below the UVLO threshold.

### 7.4.3 Operation with $V_I > 5.5 \text{ V}$

The recommended maximum input supply voltage is 5.5 V. As long as the absolute maximum voltage is not exceeded, the device will not be damaged by input supply voltages greater than 5.5 V, however, its performance is not specified.

## Device Functional Modes (continued)

### 7.4.4 Operation with EN

When EN = L the device is disabled and switching is inhibited. When EN = H the device is enabled and its start-up sequence begins. If the EN pin is left floating an internal 500-k $\Omega$  resistor pulls this pin to ground.

## 8 Application and Implementation

### NOTE

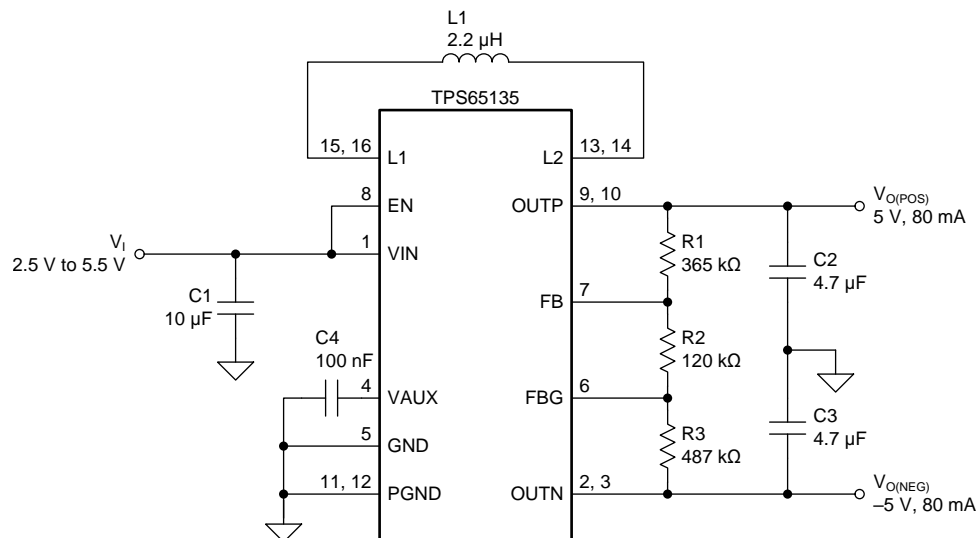
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TPS65135 device can be used to generate split-rail supplies from input supply voltages in the range 2.5 V to 5.5 V and has been optimized for use with 3.3-V rails of single-cell Li-ion batteries. It can generate positive output voltages up to 6 V and negative voltages down to  $-7$  V with buck-boost action (i.e. the input supply voltage may be above or below the positive output voltage), as long as the output current mismatch is 50% or less. Both outputs are controlled by the EN pin: a high logic level enables both outputs, and a low logic level disables them. An integrated UVLO function disables the device when the input supply voltage is too low for proper operation.

### 8.2 Typical Application

Figure 8 shows a typical application for a  $\pm 5$ -V AMOLED display supply.



Copyright © 2017, Texas Instruments Incorporated

**Figure 8. Standard Application  $\pm 5$ -V Supply**

#### 8.2.1 Design Requirements

Table 2 shows the design requirements for a  $\pm 5$ -V AMOLED supply application used as an example to illustrate the design process.

## Typical Application (continued)

**Table 2. Design Parameters**

PARAMETER	SYMBOL	EXAMPLE VALUE
Input Supply Voltage Range	$V_I$	2.5 V to 5.5 V
Positive Output Voltage	$V_{O(POS)}$	5 V
Negative Output Voltage	$V_{O(NEG)}$	-5 V
Maximum Positive Output Current	$I_{O(POS)} \text{ max}$	80 mA
Maximum Negative Output Current	$I_{O(NEG)} \text{ max}$	-80 mA

### 8.2.2 Detailed Design Procedure

#### 8.2.2.1 Choosing a Suitable Inductor

The TPS65135 device is internally compensated and operates best with a 2.2- $\mu\text{H}$  inductor. For this type of converter, selection of the inductor is a key element in the design process because it has a big impact on the efficiency, the line and load transient response, and the maximum output current the device is able to deliver. Because the inductor ripple current is fairly large in the SIMO topology, the inductor core losses largely determine converter efficiency. As a result, an inductor with a relatively large dc winding resistance (DCR) but low core losses can often achieve higher converter efficiencies than other inductors with lower DCR but higher core losses.

As previously described, the converter's line transient response is highest when the converter operates in DCM, and since larger inductor values cause the converter to enter CCM operation at lower load currents, smaller inductor values give the best line transient response. The formula to calculate the output current at which the converter enters CCM operation is shown in Equation 3. The inductors listed in Table 3 achieve a good overall converter efficiency while having a low height. The first two TOKO inductors achieve the highest efficiency (almost identical) followed by the LPS3008. The best compromise between efficiency and inductor size is given by the XFL2006 inductor. The inductor saturation current should typically be 1 A or higher, however, if the output current required by the application is low, inductors with smaller saturation current ratings may be considered.

**Table 3. Inductor Selection**

INDUCTOR VALUE	COMPONENT SUPPLIER	DIMENSIONS in mm	$I_{\text{sat}} / \text{DCR}$
2.2 $\mu\text{H}$	TOKO DFE252010C	2.5 x 2 x 1	1.9 A / 130 m $\Omega$
	TOKO DFE252012C	2.5 x 2 x 1.2	2.2 A / 90 m $\Omega$
	Coilcraft XFL2006-222	2 x 1.9 x 0.6	0.8 A / 278 m $\Omega$
	Coilcraft LPS3008-222	3 x 3 x 0.8	1.1 A / 175 m $\Omega$
	Samsung CIG2MW2R2NNE	2 x 1.6 x 1	1.2 A / 110 m $\Omega$
	TOKO FDSE0312-2R2	3.3 x 3.3 x 1.2	1.2 A / 160 m $\Omega$
	ABCO LPF3010T-2R2	2.8 x 2.8 x 1	1.0 A / 100 m $\Omega$
	Maruwa CXFU0208-2R2	2.65 x 2.65 x 0.8	0.85 A / 185 m $\Omega$

#### 8.2.2.2 Choosing Suitable Input and Output Capacitors

The TPS65135 device typically requires a 10- $\mu\text{F}$  ceramic input capacitor. Larger values can be used to lower the input voltage ripple. Table 4 lists capacitors suitable for use on the TPS65135 input.

**Table 4. Input Capacitor Selection**

CAPACITOR	COMPONENT SUPPLIER	SIZE
10 $\mu\text{F}$ / 6.3V	Murata GRM188R60J106ME84D	0603
10 $\mu\text{F}$ / 6.3 V	Taiyo Yuden JMK107BJ106	0603

A 4.7- $\mu$ F output capacitor is generally sufficient for most applications, but larger values can be used as well for improved load- and line-transient response at higher load currents. The capacitors of [Table 5](#) have been found to work well with the TPS65135 device.

**Table 5. Output Capacitor Selection**

CAPACITOR	COMPONENT SUPPLIER	SIZE
10 $\mu$ F / 6.3 V	Murata GRM188R60J106ME84D	0603
4.7 $\mu$ F / 10 V	Taiyo Yuden LMK107BJ475	0603
10 $\mu$ F / 6.3 V	Taiyo Yuden JMK107BJ106	0603

### 8.2.2.3 Choosing Suitable Feedback Resistors

[Equation 7](#) can be used to calculate a suitable value for R2, so that the recommended current of  $\approx 10 \mu$ A flows through the feedback resistors.

The value of R1 can be calculated by rearranging [Equation 7](#), so that

$$R1 = R2 \left( \frac{V_{O(POS)}}{V_{ref1}} - 1 \right) \quad (10)$$

Inserting  $R2 = 120 \text{ k}\Omega$ ,  $V_{ref1} = 1.24 \text{ V}$  and  $V_{O(POS)} = 5 \text{ V}$  into [Equation 10](#), we get

$$R1 = 120 \text{ k}\Omega \left( \frac{5 \text{ V}}{1.24 \text{ V}} - 1 \right) = 363.9 \text{ k}\Omega \quad (11)$$

The closest 1%-tolerance standard value is 365 k $\Omega$ , which will generate a nominal output voltage of 5.012 V.

The value of R3 can be calculated by rearranging [Equation 9](#), so that

$$R3 = R2 \left( \frac{|V_{O(NEG)}|}{V_{ref1}} \right) \quad (12)$$

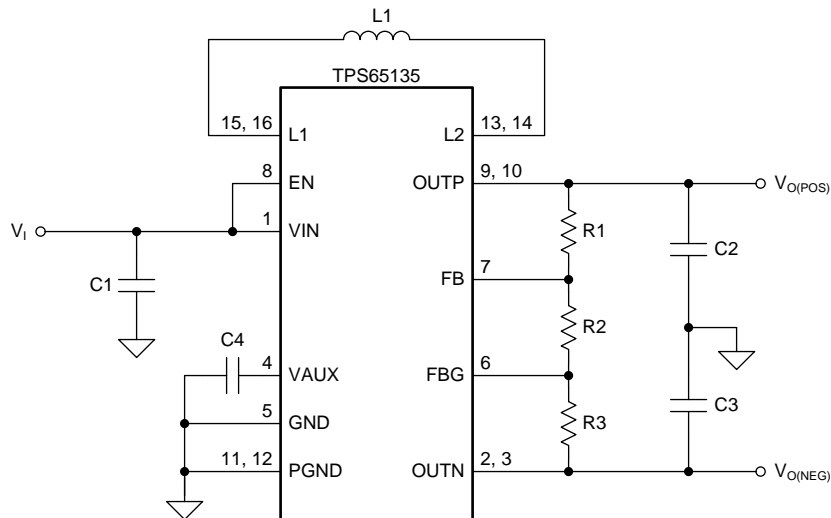
Inserting  $R2 = 120 \text{ k}\Omega$ ,  $V_{ref1} = 1.24 \text{ V}$  and  $V_{O(NEG)} = -5 \text{ V}$  into [Equation 12](#), we get

$$R3 = 120 \text{ k}\Omega \left( \frac{5 \text{ V}}{1.24 \text{ V}} \right) = 483.9 \text{ k}\Omega \quad (13)$$

The closest 1%-tolerance standard value is 487 k $\Omega$ , which will generate a nominal output voltage of  $-5.032 \text{ V}$ .

### 8.2.2.4 Measurement Circuit

The following application curves were obtained using the circuit shown in [Figure 9](#) and the external components listed in [Table 6](#).



Copyright © 2017, Texas Instruments Incorporated

Figure 9. Measurement Circuit

Table 6. Component List

Reference	Description	Manufacturer and Part Number
C1, C2, C3	10 $\mu$ F, 6.3 V, 0603, X5R, ceramic	Murata, GRM188R60J106ME84D
C4	100 nF, 10 V, 0603, X7R, ceramic	Murata, GRM188R71H104KA93D
L1	2.2 $\mu$ H, 2.2 A, 90 m $\Omega$ , 2.5 mm $\times$ 2.0 mm $\times$ 1.2 mm	Toko, 1239AS-H-2R2M
R1	Depending on the output voltage, 1%, (all measurements with $\pm$ 5 V output voltage uses 365 k $\Omega$ )	
R2	Depending on the output voltage, 1%, (all measurements with $\pm$ 5 V output voltage uses 120 k $\Omega$ )	
R3	Depending on the output voltage, 1%, (all measurements with $\pm$ 5 V output voltage uses 487 k $\Omega$ )	
U1	TPS65135RTE	Texas Instruments

### 8.2.3 Application Curves

In the following curves  $V_I = 3.7\text{ V}$ ,  $V_{O(POS)} = 5\text{ V}$ ,  $V_{O(NEG)} = -5\text{ V}$  unless otherwise noted. Where the symbol  $I_O$  is used, it implies that  $I_{O(POS)} = |I_{O(NEG)}|$ . All measurements at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

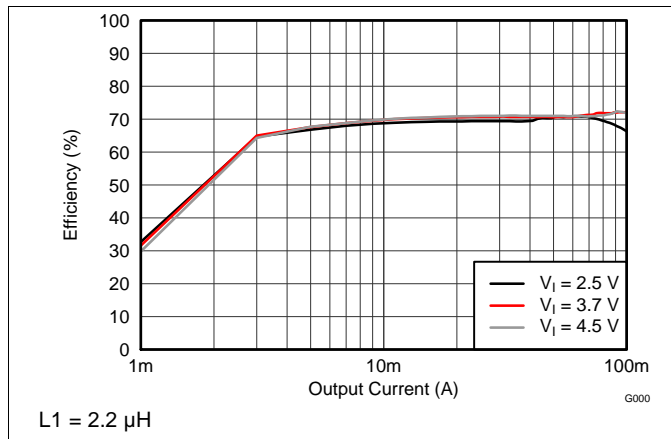


Figure 10. Efficiency vs Load Current

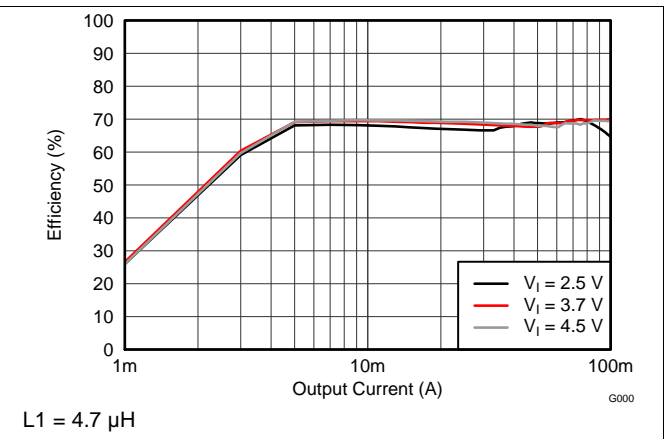


Figure 11. Efficiency vs Load Current

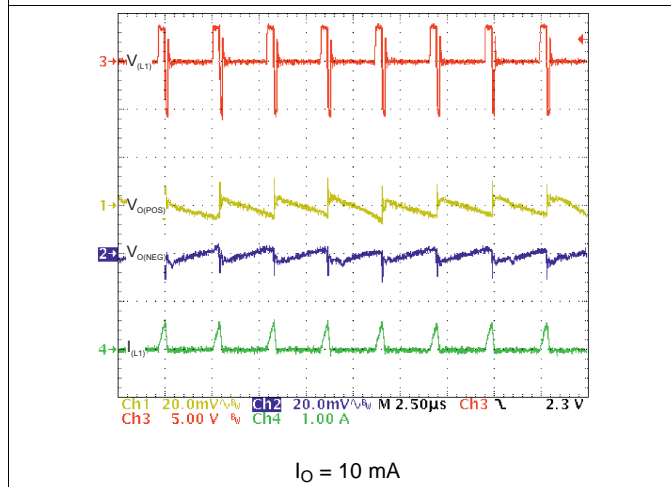


Figure 12. Operation at Light Load Current (DCM)

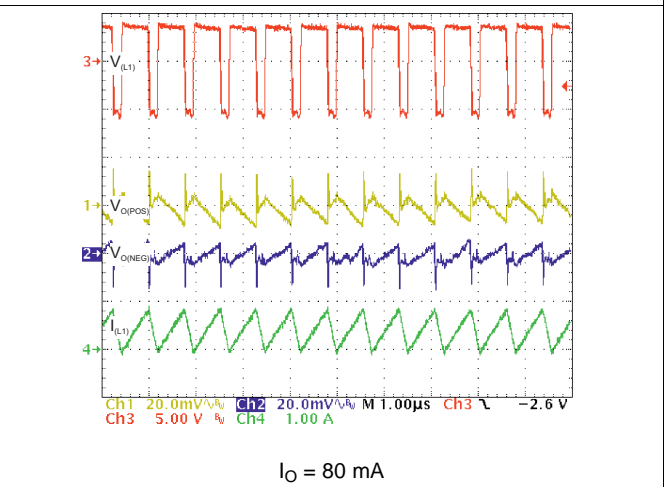


Figure 13. Operation at High Load Current (CCM)

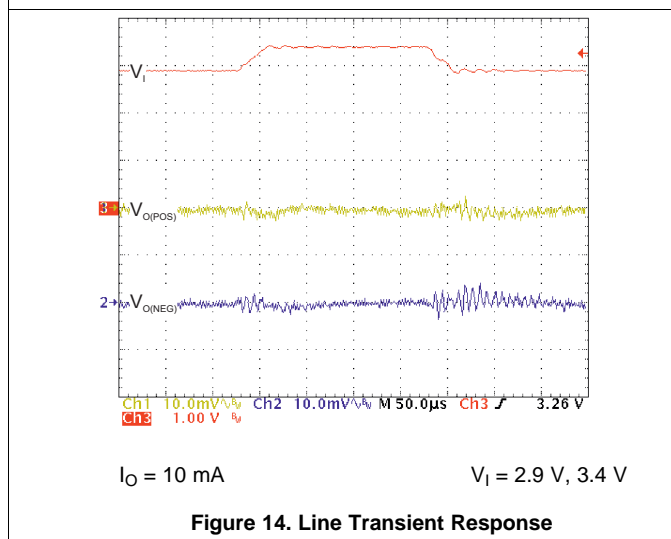


Figure 14. Line Transient Response

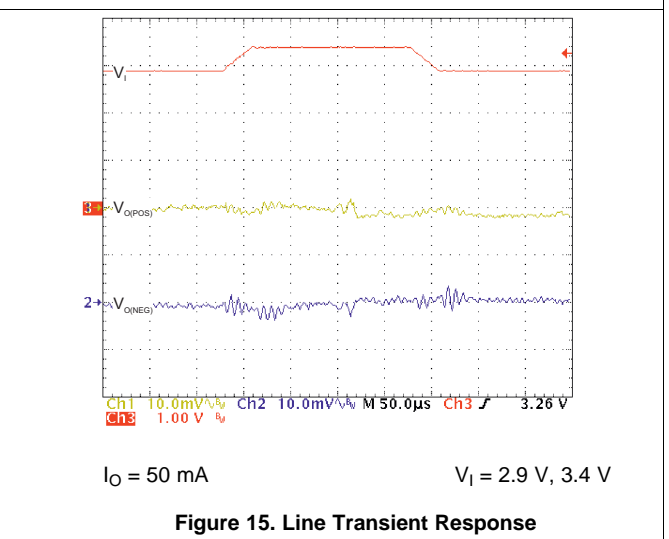
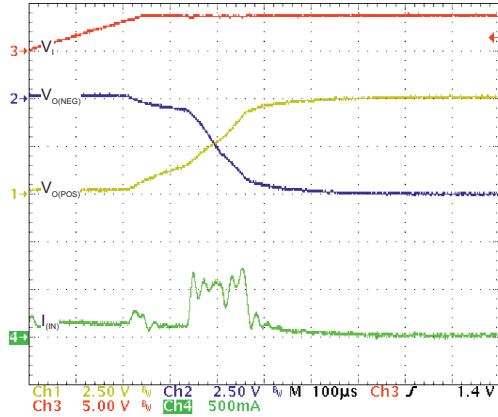


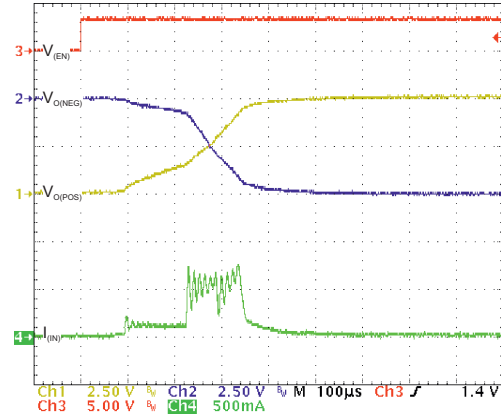
Figure 15. Line Transient Response





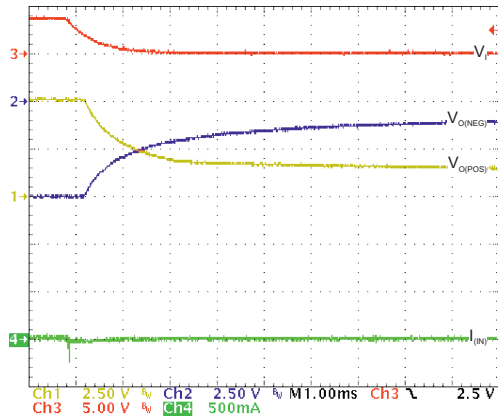
$I_O = 0 \text{ mA}$

Figure 16. Start Up ( $V_I$  Rising)



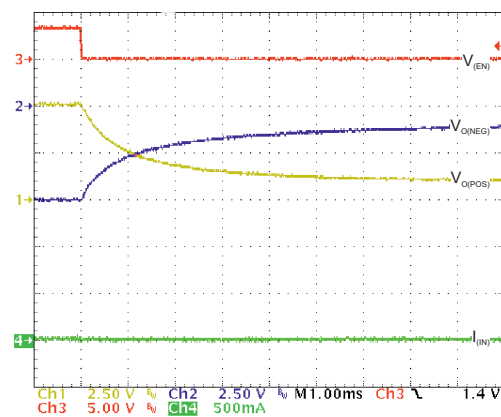
$I_O = 0 \text{ mA}$

Figure 17. Start Up ( $V_{(EN)}$  Rising)



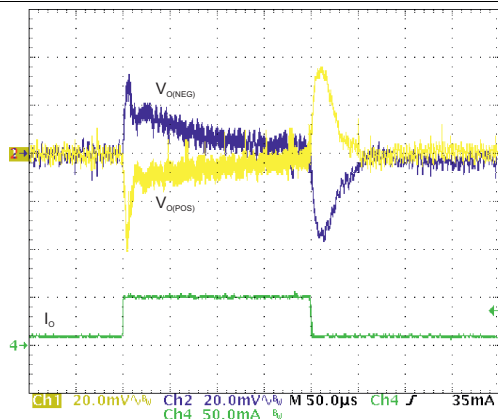
$I_O = 0 \text{ mA}$

Figure 18. Shut Down – ( $V_I$  Falling)



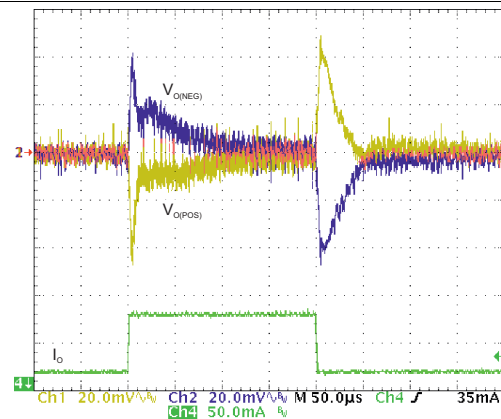
$I_O = 0 \text{ mA}$

Figure 19. Shut Down ( $V_{(EN)}$  Falling)



$I_O = 10 \text{ mA}, 50 \text{ mA}$

Figure 20. Load Transient Response



$I_O = 20 \text{ mA}, 80 \text{ mA}$

Figure 21. Load Transient Response

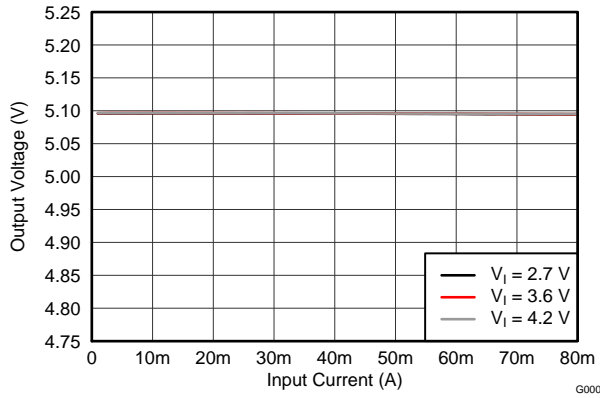


Figure 22. Positive Output Load Regulation

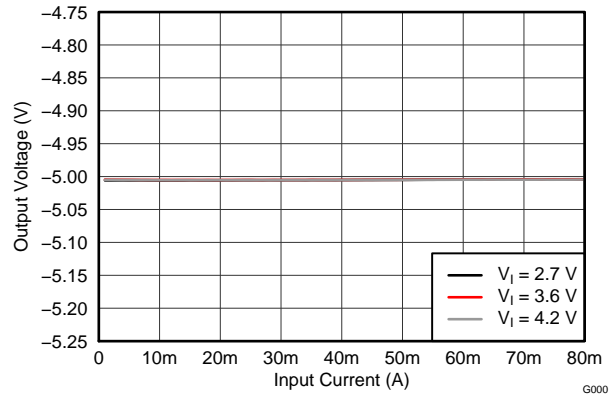


Figure 23. Negative Output Load Regulation

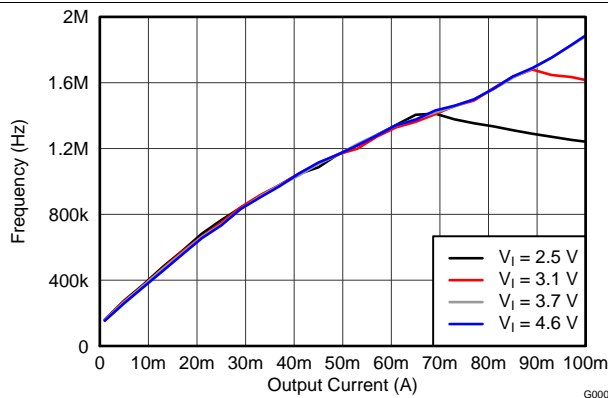


Figure 24. Switching Frequency vs Load Current

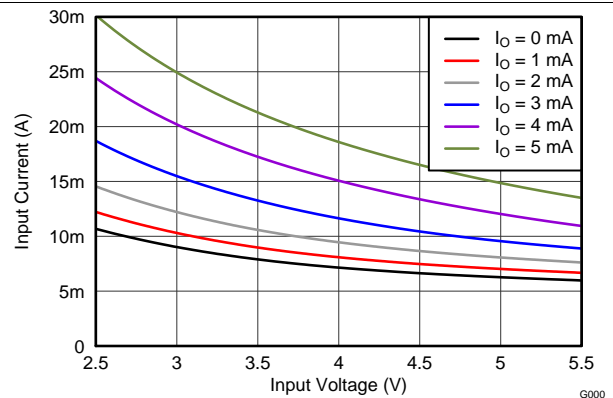


Figure 25. Input Current vs Input Voltage

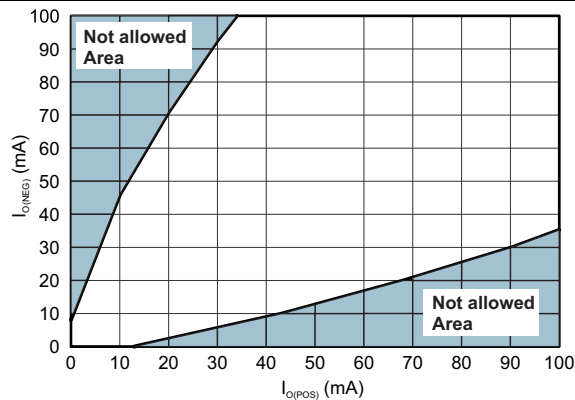


Figure 26. Output Current Mismatch

## 9 Power Supply Recommendations

The TPS65135 device is designed to operate from an input supply voltage in the range 2.5 V to 5.5 V. If the input supply is located more than a few centimeters from the device additional bulk capacitance may be required. The 10- $\mu$ F shown in the schematics in this data sheet are typical for this function.

## 10 Layout

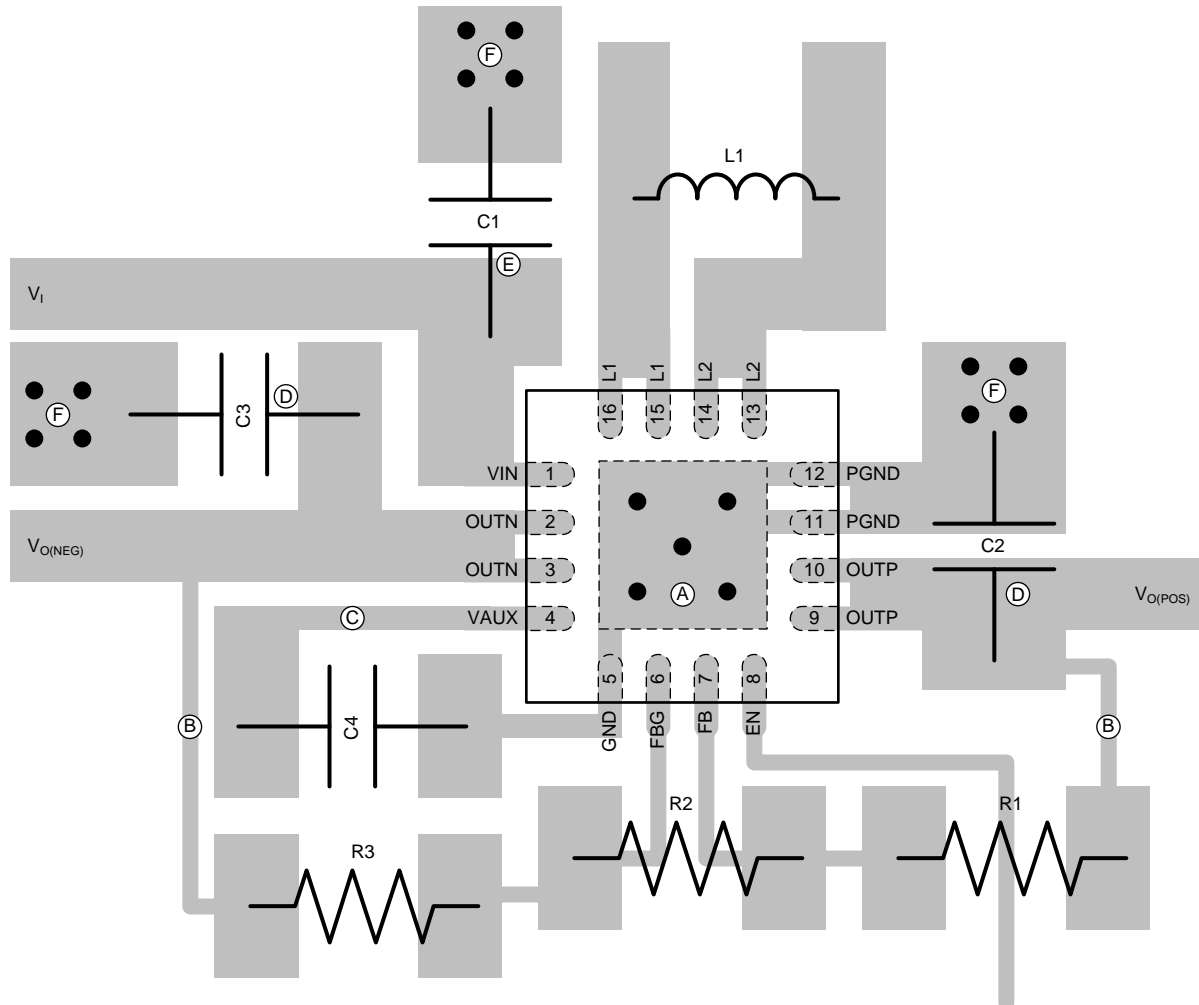
### 10.1 Layout Guidelines

No PCB layout is perfect, and compromises are always necessary. However, the basic principles listed below (in order of importance) go a long way to achieving the full performance of the TPS65135 device.

- If possible, route discontinuous switching currents on the top layer, using short, wide traces to minimize stray inductance and resistance. For the TPS65135 device, the current flowing into the VIN, L1, L2, VPOS, VNEG and PGND pins is discontinuous. In the example layout below, vias are used to connect discontinuous return currents to the ground plane, as it is considered a slightly better approach with this device than forcing all currents to flow on the top layer.
- Place C1 and C4 as close as possible to the VIN and AVIN pins respectively.
- Place C2 and C3 as close as possible to the VPOS and VNEG pins respectively.
- Place L1 as close as possible to the L1 and L2 pins.
- Use a copper pour (preferably on layer 2) as a thermal spreader and connect it to the exposed thermal pad using the maximum number of thermal vias (see packaging information for more information on the recommended thermal vias).
- The copper pour described above can be used as a ground plane if it is not possible to route power ground signals on the top layer.

## 10.2 Layout Example

Figure 27 shows an example PCB layout based on the above principles.



- (A) Multiple vias used to connect thermal pad to copper pour on bottom or inner layer to conduct heat away and minimize loop area.
- (B) Output voltages sensed directly at output capacitors. Sensing traces kept separate from high-current-carrying traces.
- (C) C4 placed close to VAUX and GND pins. Traces connecting to C4 do not need to be especially wide, because they do not conduct high current.
- (D) C2 and C3 placed close to OUTP and OUTN pins and connected with wide traces to minimize parasitic inductance.
- (E) C1 placed close to VIN pin and connected with very wide traces to minimize parasitic inductance.
- (F) PGND connected to copper pour ground plane on bottom or inner layer to minimize loop area.

**Figure 27. PCB Layout Example**

## 11 器件和文档支持

### 11.1 器件支持

#### 11.1.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

#### 11.2 接收文档更新通知

如需接收文档更新通知，请访问 [www.ti.com.cn](http://www.ti.com.cn) 网站上的器件产品文件夹。点击右上角的提醒我 (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

#### 11.3 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.4 商标

E2E is a trademark of Texas Instruments.  
All other trademarks are the property of their respective owners.

#### 11.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

#### 11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65135RTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65135RTER	WQFN	RTE	16	3000	356.0	356.0	35.0

## GENERIC PACKAGE VIEW

**RTE 16**

**WQFN - 0.8 mm max height**

3 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

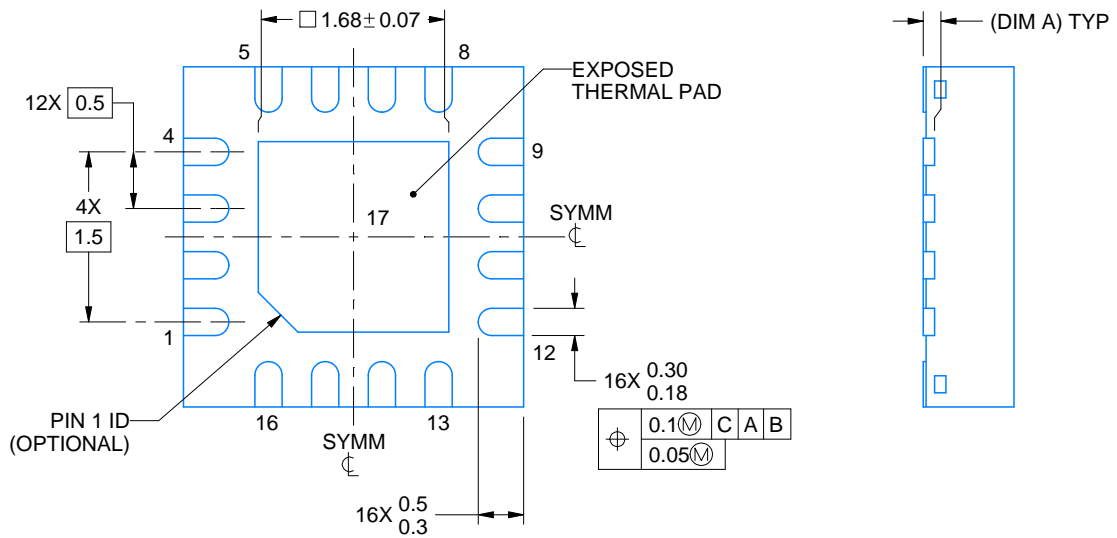


4225944/A





SIDE WALL METAL THICKNESS DIM A	
OPTION 1	OPTION 2
0.1	0.2



4219117/B 04/2022

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

RTE0016C

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:20X



SOLDER MASK DETAILS

4219117/B 04/2022

NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

RTE0016C

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



**SOLDER PASTE EXAMPLE**  
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 17:  
85% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE:25X

4219117/B 04/2022

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

## 重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265

Copyright © 2022，德州仪器 (TI) 公司